Rec'd PCT/PTO 13 OCT 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: tba
Examiner: tba

In Re PATENT APPLICATION OF

Applicant(s):	Alexandre ELLISON et al.)
Appl. No.:	10/526,259) INFORMATION
Filing Date:	February 28, 2005) DISCLOSURE) <u>STATEMENT</u>
For:	LIGHTLY DOPED SILICON CARBIDE WAFER AND USE THEREOF IN HIGH POWER DEVICES) 26694) U.S. PATENT AND) TRADEMARK OFFICE
Atty. Dkt.:	35947-213490))
		October 13, 2005

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This is an Information Disclosure Statement submitted under 37 C.F.R. § 1.97 within the time specified under 37 C.F.R. § 1.97(b).

Enclosed is a PTO-1449, and copies of references cited therein.

This Information Disclosure Statement is being filed before the mailing date of a first Office Action on the merits.

Date: (D/13/05)

Respectfully submitted,

Eric J. Franklin, Registration No. 37,134

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Substitute for form 1449A/PTO				Complete if Known		
				Application Number	10/526,059	
INFORMATION DISCLOSURE				Filing Date	February 28, 2005	
STATEMENT BY APPLICANT		First Named Inventor	Alexandre ELLISON et al.			
				Group Art Unit	tba	
(use as many sheets as necessary)			necessary)	Examiner Name	น้อล	
Sheet	1	of	1	Attorney Docket Number	35947-213490	

	U.S. PATENT DOCUMENTS						
Examiner Initials *	Cite No.1	U.S. Pa	atent Document	Name of Patentee or Applicant	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee	Date of Publication of	Pages, Columns, Lines,	
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Examiner Initials *	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
	1	J.R. JENNY, M. SKOWRONSKI, W.C. MITCHEL, H.M. HOBGOOD, R.C. GLASS, G. AUGUSTINE and R.H. HOPKINS; Optical and electrical characterization of boron impurities in silicon carbide grown by physical vapor transport; J. Appl. Phys. 79 (5), March 1996; pps. 2326-2331.	
	2	M. TRIVEDI, S. PENDHARKAR and K. SHENAI; High Temperature Performance Limits of IGBT Modules; 1998 IEEE; pps. 977-981.	
	3	AKIRA ITOH and HIROYUKI MATSUNAMI; Single Crystal Growth of SiC and Electronic Devices; Critical Reviews in Solid State and Materials Sciences; 1997; 22(2); pps. 111-197; CRC Press LLC.	

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